



ALTERNATIVE TO PTO/SB/08a/b (07-05)

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known			
		Application Number	10/722,576		
		Filing Date	November 28, 2003		
		First Named Inventor	Thomas Happ		
		Art Unit	2187		
		Examiner Name	K. N. McLean Mayo		
Sheet	1	of	1	Attorney Docket Number	543822002600

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
KMM	1.	2003/0084233-A1	05-01-2003	WILLIAMS	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
KMM	2.	Hirose, Y. et al. (1976). "Polarity-dependent Memory Switching and Behavior of Ag Dendrite in Ag-photodoped Amorphous As ₂ S ₃ Films," <i>Journal of Applied Physics</i> 47(6):2767-2772.	
	3.	Kozicki, M. N. et al. (1999). "Application of Programmable Resistance Changes in Metal-doped Chalcogenides," <i>Electrochemical Society Proceedings</i> 99(13):298-309.	
	4.	Kozicki, M. N. et al. (2000). "Nanoscale Effects in Devices Based on Chalcogenide Solid Solutions," <i>Superlattices and Microstructures</i> 27(5/6):485-488.	
	5.	Kozicki, M. N. et al. (2002). "Can Solid State Electrochemistry Eliminate the Memory Scaling Quandry," <i>Proc. VLSI</i> 15 pages.	
	6.	Neale, R. (2002). "Micron to Look Again at Non-volatile Amorphous Memory," <i>Electronic Engineering Design</i> 6 pages.	

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	<i>K. N. McLean Mayo</i>	Date Considered	November 9, 2007
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